



**SIDDHARTH GROUP OF INSTITUTIONS :: PUTTUR**  
Siddharth Nagar, Narayanavanam Road – 517583

**QUESTION BANK (DESCRIPTIVE)**

**Subject with Code :** Electronic Circuit Analysis (16EC407)

**Course & Branch:** B.Tech - ECE

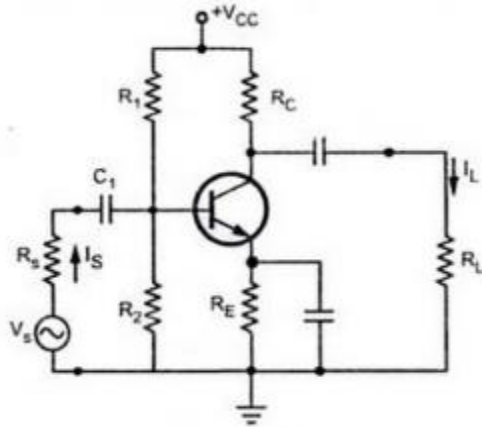
**Year & Sem:** II-B.Tech & II-Sem

**Regulation:** R16

**UNIT –I**

**SMALL SIGNAL LOW FREQUENCY TRANSISTOR AMPLIFIER ANALYSIS**

1. a) Why hybrid model is used for the analysis of BJT amplifier at low frequencies? Draw the hybrid model for CE transistor and derive the parameters. [6M]  
b) Compare the CE, CB and CC transistor amplifier parameters. [6M]
2. Using low frequency h-parameter model, derive the expressions for voltage gain, current gain, input impedance and output admittance for a BJT Amplifier in CE configuration. [12M]
3. a) With neat diagram, derive the CE amplifier parameters using approximate analysis. [6M]  
b) Obtain the expressions for current gain, voltage gain, input impedance and output impedance of CB amplifier using simplified hybrid model. [6M]
4. a) Determine the parameters  $A_i$ ,  $R_i$ ,  $A_v$  and  $R_o$  of Emitter Follower using simplified hybrid model analysis. [6M]  
b) A voltage source of internal resistance  $R_s = 900\Omega$  drives a CC amplifier using load resistance  $R_L = 2000\Omega$ . The CE h parameters are  $h_{fe} = 60$ ,  $h_{ie} = 1200\Omega$ ,  $h_{oe} = 25\mu A/V$  and  $h_{re} = 2 \times 10^{-4}$ . Compute  $A_i$ ,  $R_i$ ,  $A_v$  and  $R_o$  using approximate analysis. [6M]
5. A CE amplifier is driven by a voltage source of internal resistance  $R_s = 800\Omega$  and the load impedance of  $R_L = 1000\Omega$ . The h-parameters are  $h_{ie} = 1k$ ,  $h_{fe} = 50$ ,  $h_{oe} = 25\mu A/V$  and  $h_{re} = 2 \times 10^{-4}$ . Calculate current gain, voltage gain, input impedance and output impedance using exact analysis and approximate analysis. [12M]
6. Consider a single stage CE amplifier with  $R_s = 1k\Omega$ ,  $R_1 = 50k\Omega$ ,  $R_2 = 2k\Omega$ ,  $R_c = 1k\Omega$ ,  $R_L = 1.2k\Omega$ ,  $h_{fe} = 50$ ,  $h_{ie} = 1.1k$ ,  $h_{oe} = 25\mu A/V$  and  $h_{re} = 2.5 \times 10^{-4}$ , as shown in Fig. Find  $A_i$ ,  $R_i$ ,  $A_v$ ,  $A_{vs}$ ,  $A_{IS}$  and  $R_o$ . [12M]



7. a) Obtain the expression for current gain, voltage gain, input impedance and output impedance for Common Emitter Amplifier with Emitter Resistor. [6M]
- b) A CE amplifier is driven by a voltage source of internal resistance  $R_s = 1000\Omega$  and the load impedance of  $R_C = 2k\Omega$ . The h-parameters are  $h_{ie} = 1.3k$ ,  $h_{fe} = 55$ ,  $h_{oe} = 22\mu A/V$  and  $h_{re} = 2 \times 10^{-4}$ . Neglecting biasing resistors, compute current gain, voltage gain, input impedance, output impedance for the value of Emitter Resistor  $R_E = 200\Omega$  inserted in the emitter circuit. [6M]
8. a) Draw the circuit diagram of a single stage RC coupled Amplifier and discuss the steps used for designing it. [6M]
- b) Determine Voltage Gain, Current Gain, Input resistance and Output resistance for a CE amplifier using NPN transistor with  $h_{ie} = 1200\Omega$ ,  $h_{re} = 0$ ,  $h_{fe} = 36$  and  $h_{oe} = 2 \times 10^{-6}$  mhos,  $R_L = 2.5k\Omega$  and  $R_s = 500\Omega$  (neglect the effect of biasing circuit). [6M]
9. Design a single stage RC coupled BJT amplifier for the following values. Assume that for Silicon transistor,  $V_{cc} = 10V$ ,  $I_c = 4mA$ ,  $h_{fe} = 100$ ,  $h_{ie} = 1k\Omega$ ,  $R_{L'} = 100k\Omega$  and  $f_L = 100Hz$ . [12M]
10. a) Draw the circuit diagram of JFET Common Source amplifier with voltage divider bias for bypassed  $R_s$  and determine the expression for input impedance, output impedance and voltage gain. [6M]
- b) Derive input impedance, output impedance and voltage gain of JFET Common Drain amplifier with neat diagram. [6M]

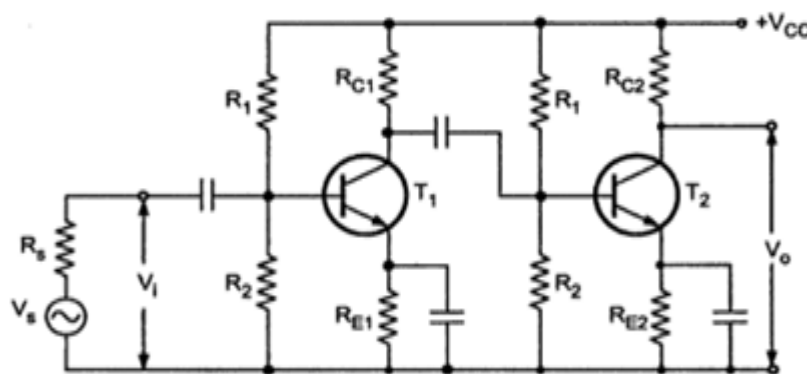
## UNIT –II

## SMALL SIGNAL HIGH FREQUENCY TRANSISTOR AMPLIFIER ANALYSIS

1. a) Draw the Hybrid- $\pi$  model and explain the significance of each and every component in it. [6M]  
 b) Derive the expression for Hybrid-  $\pi$  capacitance of CE transistor at high frequency. [6M]
2. Derive the expressions for the hybrid  $\pi$  parameters  $g_m$ ,  $g_{b'e}$ ,  $g_{b'c}$ ,  $r_{bb'}$  and  $g_{ce}$ . [12M]
3. a) Mention the typical values of Hybrid-  $\pi$  parameters. [6M]  
 b) A BJT  $g_m = 38\text{mS}$ ,  $r_{b'e} = 5.9\text{k}\Omega$ ,  $h_{ie} = 6\text{k}\Omega$ ,  $r_{bb'} = 100\Omega$ ,  $C_{b'c} = 12\text{pF}$ ,  $C_{b'e} = 63\text{pF}$  and  $h_{fe} = 224$  at 1 kHz. Calculate  $f_{\alpha}$ ,  $f_{\beta}$  and  $f_T$  cutoff frequencies. [6M]
4. With the help of necessary circuit diagrams and approximations obtain the expression for CE Short circuit current gain and derive the relation between  $f_{\beta}$  and  $f_T$ . [12M]
5. a) Discuss the dependency of hybrid- $\pi$  parameters upon collector current,  $V_{CE}$  and Temperature. [6M]  
 b) A BJT has the following parameters measured at  $I_c=1\text{mA}$ ,  $h_{ie}=3\text{k}\Omega$ ,  $h_{fe}=100$ ,  $C_c=2\text{pF}$  and  $C_e=18\text{pF}$ . Find  $g_m$ ,  $r_{b'e}$ , and  $r_{bb'}$  for  $R_L=1\text{K}\Omega$ . [6M]
6. a) At  $I_c = 1\text{mA}$  and  $V_{CE}=10\text{V}$ , a certain transistor data shows  $C_c = C_{b'c} = 3\text{pF}$ ,  $h_{fe} = 200$  and  $\omega_T = -500\text{M rad/sec}$ . Calculate  $g_m$ ,  $r_{b'e}$ ,  $C_e = C_{b'e}$  and  $\omega_{\beta}$ . [10M]  
 b) Define Unity Gain Frequency  $f_T$ . [2M]
7. Obtain the expression for Current gain with load resistor and explain the variation of frequency Response with  $R_L$ . [12M]
8. a) Short circuit CE current gain of a transistor is 25 at a frequency of 2MHz. If  $f_{\beta} = 200\text{KHz}$  Calculate (i)  $f_T$  (ii)  $h_{fe}$  (iii) Find  $|A_i|$  at frequency of 10MHz and 100MHz. [6M]  
 b) Derive the expression for cut off frequencies  $f_{\alpha}$ ,  $f_{\beta}$  and  $f_T$ . [6M]
9. a) Describe the relationship between low frequency h-parameters and high frequency Parameters. [8M]  
 b) Write about Collector junction capacitance and Emitter junction capacitance of hybrid- $\pi$  model. [4M]
10. A transistor has  $h_{ie} = 6\text{k}\Omega$  and  $h_{fe} = 224$  at  $I_C = 1\text{mA}$ , with  $f_T = 80\text{MHz}$  and  $C_{b'c} = 12\text{pF}$ . Determine  $g_m$ ,  $r_{b'e}$ ,  $r_{bb'}$  and  $C_{b'e}$  at room temperature. [12M]

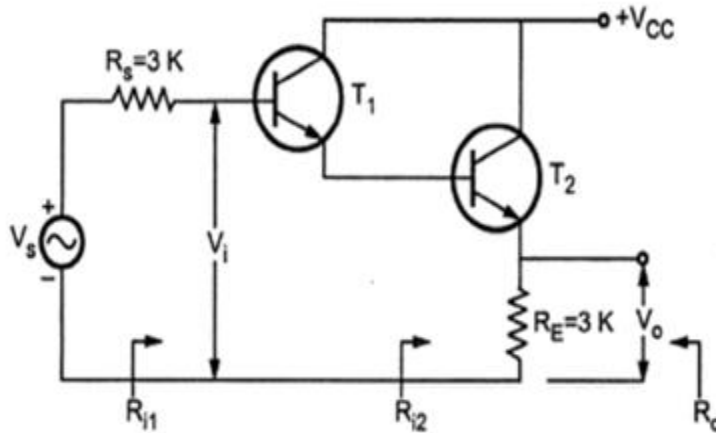
**UNIT -III**  
**MULTISTAGE AMPLIFIERS**

1. (a) Explain the classification of amplifiers. [6M]  
(b) Discuss the need of cascading amplifiers. [6M]
2. Describe different methods used for coupling multistage amplifiers with their frequency response. [12M]
3. Draw the block diagram of n-stage cascaded amplifier and analyze its various parameters. [12M]
4. Analyze Two stage RC coupled amplifier with neat diagrams. [12M]
5. With neat diagram explain cascode amplifier and derive the overall voltage gain of cascode amplifier. [12M]
6. a) What is Darlington Connection? Mention the advantages of Darlington Pair Amplifier. [4M]  
b) With diagram, derive the expression for current gain and input resistance of Darlington amplifier. [8M]
7. Explain how the input impedance is increased by Bootstrap Emitter Follower with neat diagram. [12M]
8. a) Explain the effect of cascading of amplifiers on bandwidth. [6M]  
b) An amplifier consists of 3 identical stages in cascade, the bandwidth of overall amplifier extends from 20 Hz to 20 kHz. Calculate the bandwidth of individual stage. [6M]
9. The following figure shows CE-CE cascade amplifier with their biasing arrangements. Calculate  $R_i$ ,  $A_i$ ,  $A_v$ ,  $R_i'$ ,  $A_{v_s}$  and  $A_{i_s}$  if circuit parameters are:  $R_s=1K$ ,  $R_{C1} = 15K$ ,  $R_{E1}= 100\Omega$ ,  $R_{C2} = 4 K\Omega$ ,  $R_{E2} = 330\Omega$  with  $R_1 = 200K$  and  $R_2 = 20K$  for first stage and  $R_1 = 47K$  and  $R_2 = 4.7K$  for second stage. Assume that  $h_{ie} = 1.2k\Omega$ ,  $h_{fe} = 50$ ,  $h_{re} = 2.5 \times 10^{-4}$  and  $h_{oe} = 25 \times 10^{-6}$  A/V. [12M]



**Fig. CE-CE Cascade amplifier**

10. For the circuit shown in Fig. Calculate  $R_i$ ,  $A_i$ ,  $A_v$  and  $R_o$ .  $h_{ie}=1.1k$ ,  $h_{fe}=50$ ,  $h_{oe} = 25\mu A/V$  and  $h_{re} = 2.5 \times 10^{-4}$ . [12M]



#### UNIT -IV

#### FEEDBACK AMPLIFIERS AND OSCILLATORS

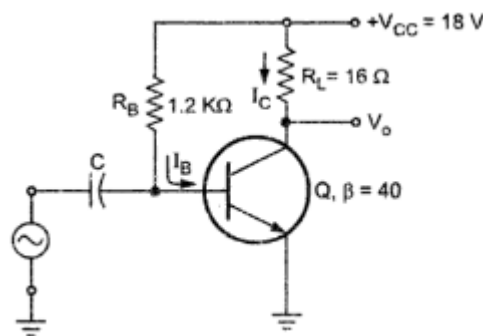
1. Explain the characteristics of negative feedback amplifiers. [12M]
2. a) Discuss Feedback topologies. [6M]
  - b) An amplifier has an open loop gain of 1000 and a feedback ratio of 0.04. If the open loop gain changes by 10% due to temperature, find the percentage change in gain of the amplifier with feedback. [6M]
3. a) Derive the expressions of input and output resistances for Voltage Series FBA. [6M]
  - b) Determine the input and output resistances of Current Shunt feedback amplifier. [6M]
4. a) Derive the expressions of input and output resistances for Voltage Shunt FBA. [6M]
  - b) Determine the input and output resistances of Current Series feedback amplifier. [6M]
5. a) An amplifier has a voltage gain of 400,  $f_1 = 50$  Hz,  $f_2 = 200$ kHz and a distortion of 10% without feedback. Determine the amplifier voltage gain,  $f_{1f}$ ,  $f_{2f}$  and  $D_f$  when a negative feedback is applied with feedback ratio of 0.01. [6M]
  - b) A voltage series negative feedback amplifier has a voltage gain without feedback of  $A = 500$ , input resistance  $R_i = 3k\Omega$ , output resistance  $R_o = 20k\Omega$  and feedback ratio  $\beta = 0.01$ . Calculate the voltage gain  $A_f$ , input resistance  $R_{if}$ , and output resistance  $R_{of}$  of the amplifier with feedback. [6M]
6. a) State Barkhausen Criterion for oscillations. Explain the principle of operation of oscillator. [6M]
  - b) Classify the different types of oscillators. [6M]

7. a) Derive the expression for frequency of oscillations for RC phase shift Oscillator. [6M]  
 b) Discuss the working principle of Wein bridge oscillator and derive the expression for frequency of oscillations. [6M]
8. a) With neat diagram, explain Hartley Oscillator and derive the expression for frequency of oscillation. [6M]  
 b) Discuss Colpitts Oscillator and obtain the expression for frequency of oscillation. [6M]
9. a) Give the general analysis of an LC Oscillator. [6M]  
 b) Draw the equivalent circuit of a Quartz Crystal and explain its principle of operation with the help of neat circuit diagram. [6M]
10. a) Explain the concept of stability of Oscillators. [6M]  
 b) In the Hartley oscillator,  $L_2 = 0.4\text{mH}$  and  $C = 0.004\ \mu\text{F}$ . If the frequency of the oscillator is 120 kHz, find the value of  $L_1$ . Neglect the mutual inductance. [6M]

## UNIT V

### POWER AMPLIFIERS & TUNED AMPLIFIERS

1. a) With neat diagram explain Series fed, Directly coupled Class A Power Amplifier and derive its maximum efficiency. [6M]  
 b) A series fed Class A amplifier shown in Fig, operates from dc source and applied sinusoidal input signal generates peak base current 9mA. Calculate : (i) Quiescent current  $I_{CQ}$ , (ii) Quiescent voltage  $V_{CEQ}$ , (iii) DC input power  $P_{DC}$ , (iv) AC output power  $P_{AC}$  and (v) Efficiency. [6M]



2. a) Discuss with diagram, Transformer coupled Class A Power Amplifier and derive its Maximum efficiency. [6M]  
 b) Explain second harmonic distortion by three point method. [6M]
3. a) Describe Higher order harmonic distortion by five point method. [6M]  
 b) With neat diagram explain Push Pull Class B Power Amplifier and derive its maximum

- efficiency. [6M]
4. a) Describe Complementary Symmetry Class B Power Amplifier with diagram and write about crossover distortion in class B power amplifiers. [6M]
- b) A class B push pull amplifier supplies power to a resistive load of  $12\Omega$ . The output transformer has a turns ratio of 3:1 and efficiency of 78.5%. Obtain (i) Maximum power output, (ii) maximum power dissipation in each transistor and (iii) Maximum base and collector current. For each transistor, assume  $h_{fe} = 25$  and  $V_{CC} = 20V$ . [6M]
5. a) Write notes on Class AB operation. [6M]
- b) Discuss the need of Heat sink for power transistors. Mention about thermal stability of power transistors. [6M]
6. a) Compare Single Tuned and Double Tuned Amplifier. [2M]
- b) Describe the operation of a single tuned capacitive coupled amplifier with diagram and derive the expression for its centre frequency, Quality factor, Voltage gain and bandwidth. [12M]
7. Discuss Double Tuned Amplifier with neat diagram and derive the expression for its bandwidth. [12M]
8. a) Explain the effect of cascading single tuned amplifiers on bandwidth. [6M]
- b) The bandwidth of single tuned amplifier is 20kHz. Calculate the bandwidth if such three stages are cascaded. Also calculate the bandwidth for four stages. [6M]
9. a) With circuit diagram, explain the stagger tuning operation. Give necessary graph. [6M]
- b) Explain the stability considerations of a tuned amplifier. [6M]
10. a) A single tuned RF amplifier uses a transistor with an output resistance of  $50\text{ K}\Omega$ , output capacitance of  $15\text{ pF}$  and internal resistance of next stage is  $20\text{ k}\Omega$ . The tuned circuit consists of  $47\text{ pF}$  capacitance in parallel with series combination of  $1\mu\text{H}$  inductance and  $2\Omega$  resistance. Calculate resonant frequency, effective quality factor and bandwidth of the circuit. [6M]
- b) Explain the advantages, disadvantages and applications of Tuned Amplifiers. [6M]

**Prepared by:**

**1. Dr. P.RATNA KAMALA**

**Professor/ECE**

**2. Mr M. AFSAR ALI**

**Professor/ECE**